

In the Claims:

Please amend Claims 39 and 41; and cancel Claims 1-38 and 44-74 as follows:

1-38. (Cancelled)

39. (Currently Amended)) A method for fabricating a liquid crystal display device including a liquid crystal layer clamped between a first substrate and a second substrate, said method comprising the steps of:

- (a) forming a pixel electrode pattern on said first substrate;
- (b) painting a resist film on said pixel electrode pattern;
- (c) exposing and developing said resist film and forming a resist pattern having a shape, in which multiple blanches are repeated, on said pixel electrode pattern;
- (d) conducting an ashing process for said resist pattern; and
- (e) conducting a thermosetting process for said ~~resist~~ashing pattern that said assign process conducted;

so that liquid crystal molecules in said liquid crystal layer orient approximately in vertical to a surface of said liquid crystal layer in a non-driving state in which a driving electric field is not applied to said liquid crystal layer, and said liquid crystal molecules orient approximately in parallel to said surface of said liquid crystal layer in a driving state in which the driving electric field is applied to said liquid crystal layer.

40. (Original) The method as claimed in claim 39, wherein said step (c) includes the step of exposing said resist film at less than double exposure amount of an exposure threshold for said resist film.

41. (Currently Amended) The method as claimed in claim 39, wherein said step (b) includes the step of forming said resist film having such a thickness that a thickness of said resist pattern is in a range from ~~100 μm~~ 100 nm to ~~1700 μm~~ 1700 nm after said ashing process.

42. (Original) The method as claimed in claim 39, wherein said step (b) includes the step of adjusting a viscosity of said resist film so that a thickness of said resist film is in a range from 600nm to 800nm.

43. (Original) The method as claimed in claim 39, wherein said step (e) includes the step of starting the thermosetting process at a temperature lower than 140°C and gradually rising the temperature up to a thermosetting temperature that is lower than 270°C.

44-74. (Cancelled)